

# Jerzy Kanicki

## List of Publications by Year in descending order

Source: [//exaly.com/author-pdf/4143314/publications.pdf](https://exaly.com/author-pdf/4143314/publications.pdf)

Version: 2025-02-01

227  
papers

4,480  
citations

73894

38  
h-index

121293

58  
g-index

236  
all docs

236  
docs citations

236  
times ranked

3246  
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at $R = 2\%$ mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 913-916.	4.3	13
2	Cascaded systems analysis of a-Se/a-Si and a-InGaZnO TFT passive and active pixel sensors for tomosynthesis. Physics in Medicine and Biology, 2019, 64, 025012.	3.5	7
3	Novel Top-Anode OLED/a-IGZO TFTs Pixel Circuit for 8K4K AM-OLEDs. IEEE Transactions on Electron Devices, 2019, 66, 436-444.	3.3	20
4	Photoluminescence Study of Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2018, 65, 1258-1261.	3.3	4
5	High-performance PBT7-Th:PC70BM polymer photodiode with transferred charge blocking layers. Organic Electronics, 2018, 62, 566-571.	2.6	6
6	Physical origin of the non-linearity in amorphous In-Ga-Zn-O thin-film transistor current-voltage characteristics. Solid-State Electronics, 2018, 147, 51-57.	1.4	3
7	Study of current-mode active pixel sensor circuits using amorphous InSnZnO thin-film transistor for 50- $\mu$ m pixel-pitch indirect X-ray imagers. Solid-State Electronics, 2017, 131, 53-64.	1.4	11
8	Task-Based Modeling of a 5k Ultra-High-Resolution Medical Imaging System for Digital Breast Tomosynthesis. IEEE Transactions on Medical Imaging, 2017, 36, 1820-1831.	10.3	5
9	Bilayer Interdiffused Heterojunction Organic Photodiodes Fabricated by Double Transfer Stamping. Advanced Optical Materials, 2017, 5, .	7.1	20
10	3D Printed Masks and Transfer Stamping Process to Enable the Fabrication of the Hemispherical Organic Photodiodes. Advanced Materials Technologies, 2017, 2, .	6.1	5
11	DNA-DODA-based polymer electrolytes for dye sensitized solar cells. Molecular Crystals and Liquid Crystals, 2017, 655, 131-141.	1.2	0
12	Response to "Comment on "Large area CMOS active pixel sensor x-ray imager for digital breast tomosynthesis: Analysis, modeling, and characterization" [Med. Phys. 43, 1578-1579 (2016)]. Medical Physics, 2016, 43, 6210-6212.	1.4	0
13	Amorphous InSnZnO Thin-Film Transistor Voltage-Mode Active Pixel Sensor Circuits for Indirect X-Ray Imagers. IEEE Transactions on Electron Devices, 2016, 63, 4802-4810.	3.3	17
14	Half-Corbino short-channel amorphous InGaZnO thin-film transistors with a-SiO <sub>x</sub> or a-SiO <sub>x</sub> /a-SiN <sub>x</sub> passivation layers. Solid-State Electronics, 2016, 120, 25-31.	1.4	16
15	Influence of DNA and DNA-PEDOT: PSS on dye sensitized solar cell performance. Molecular Crystals and Liquid Crystals, 2016, 627, 38-48.	1.2	11
16	DC sputtered amorphous InGaZnO thin-film transistors: Electrical properties and stability. Solid-State Electronics, 2016, 116, 22-29.	1.4	49
17	Large area CMOS active pixel sensor x-ray imager for digital breast tomosynthesis: Analysis, modeling, and characterization. Medical Physics, 2015, 42, 6294-6308.	3.4	43
18	Density of states of short channel amorphous InGaZnO thin-film transistor arrays fabricated using manufacturable processes. Japanese Journal of Applied Physics, 2015, 54, 051101.	2.0	9

#	ARTICLE	IF	CITATIONS
19	Comparison of composition and atomic structure of amorphous indium gallium zinc oxide thin film transistor before and after positive bias temperature stress by transmission electron microscopy. Semiconductor Science and Technology, 2015, 30, 055008.	2.3	3
20	Dynamic Response of a-InGaZnO and Amorphous Silicon Thin-Film Transistors for Ultra-High Definition Active-Matrix Liquid Crystal Displays. Journal of Display Technology, 2015, 11, 471-479.	1.6	24
21	Top illuminated organic photodetectors with dielectric/metal/dielectric transparent anode. Organic Electronics, 2015, 20, 103-111.	2.6	30
22	Short channel amorphous In <sup>0.4</sup> Ga <sup>0.4</sup> Zn <sup>0.2</sup> O thin-film transistor arrays for ultra-high definition active matrix liquid crystal displays: Electrical properties and stability. Solid-State Electronics, 2015, 111, 67-75.	1.4	24
23	Electrochromic device with Prussian blue and HPC-based electrolyte. Electrochimica Acta, 2015, 182, 878-883.	5.4	18
24	50 $\mu\text{m}$ pixel pitch wafer-scale CMOS active pixel sensor x-ray detector for digital breast tomosynthesis. Physics in Medicine and Biology, 2015, 60, 8977-9001.	3.5	27
25	Tetrabenzoporphyrin Organic Semiconductors for Flexible Organic Thin Film Transistors and Circuits. , 2015, , .		0
26	White Light-Emitting Device on Flexible Plastic Substrates. , 2015, , .		0
27	Nitrogen Dangling Bonds in Hydrogenated Amorphous Silicon Nitride Thin Films. , 2015, , .		0
28	Bias-Stress-Induced Stretched-Exponential Time Dependence of Charge Injection and Trapping in Amorphous Silicon Thin-Film Transistors. , 2015, , .		0
29	A Simple Polysilicon Thin Film Transistor Structure for Achieving High On/Off Current Ratio Independent of Gate Bias. , 2015, , .		1
30	Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon TFT Characteristics. , 2015, , .		0
31	Impedance Analysis of Gellan Gum - Poly(vinyl pyrrolidone) Membranes. Molecular Crystals and Liquid Crystals, 2014, 604, 84-95.	1.2	10
32	Oxygen flow effects on electrical properties, stability, and density of states of amorphous In <sup>0.4</sup> Ga <sup>0.4</sup> Zn <sup>0.2</sup> O thin-film transistors. Japanese Journal of Applied Physics, 2014, 53, 121101.	2.0	32
33	Properties of Electrodeposited WO <sub>3</sub> Thin Films. Molecular Crystals and Liquid Crystals, 2014, 604, 71-83.	1.2	24
34	Electrical Instability of Double-Gate a-IGZO TFTs With Metal Source/Drain Recessed Electrodes. IEEE Transactions on Electron Devices, 2014, 61, 1109-1115.	3.3	26
35	AC Bias-Temperature Stability of a-InGaZnO Thin-Film Transistors With Metal Source/Drain Recessed Electrodes. IEEE Transactions on Electron Devices, 2014, 61, 806-812.	3.3	9
36	Density of states of amorphous In-Ga-Zn-O from electrical and optical characterization. Journal of Applied Physics, 2014, 116, .	2.3	63

#	ARTICLE	IF	CITATIONS
37	P <sub>25</sub> : Top Gate Amorphous In <sub>2</sub> Ga <sub>2</sub> Zn <sub>2</sub> O Thin Film Transistors Fabricated on Soda-Lime-Silica Glass Substrates. Digest of Technical Papers SID International Symposium, 2014, 45, 1035-1038.	0.5	3
38	An a-InGaZnO TFT Pixel Circuit Compensating Threshold Voltage and Mobility Variations in AMOLEDs. Journal of Display Technology, 2014, 10, 402-406.	1.6	28
39	Two-Dimensional Numerical Simulation of Bottom-Gate and Dual-Gate Amorphous In-Ga-Zn-O MESFETs. IEEE Electron Device Letters, 2014, 35, 75-77.	4.3	17
40	Amorphous In <sub>2</sub> Ga <sub>2</sub> Zn <sub>2</sub> O thin-film transistor active pixel sensor x-ray imager for digital breast tomosynthesis. Medical Physics, 2014, 41, .	3.4	47
41	High Efficiency Cu(In,Ga)Se <sub>2</sub> Flexible Solar Cells Fabricated by Roll-to-Roll Metallic Precursor Co-sputtering Method. Japanese Journal of Applied Physics, 2013, 52, 092302.	2.0	14
42	Dynamic response of amorphous In-Ga-Zn-O thin-film transistors for 8K&#x00D7;4K flat-panel display. , 2013, , 1-2.		2
43	16.3: AC and DC Bias-Temperature Stability of Coplanar Homojunction a-InGaZnO Thin-Film Transistors. Digest of Technical Papers SID International Symposium, 2013, 44, 174-177.	0.5	3
44	High performance amorphous metal-oxide semiconductors thin-film passive and active pixel sensors. , 2013, , 27.3.1-27.3.4.		8
45	Ab initio electronic structure calculations of solid, solution-processed metallotetrabenzoporphyrins. Journal of Applied Physics, 2012, 111, 073709.	2.3	4
46	P <sub>14</sub> : a-InGaZnO TFT Based Pixel Circuits for AMOLED Displays. Digest of Technical Papers SID International Symposium, 2012, 43, 1097-1100.	0.5	5
47	Solution-processed zinc tetrabenzoporphyrin thin-films and transistors. Thin Solid Films, 2012, 520, 4031-4035.	1.9	15
48	Amorphous In <sub>2</sub> Ga <sub>2</sub> Zn <sub>2</sub> O Dual-Gate TFTs: Current-Voltage Characteristics and Electrical Stress Instabilities. IEEE Transactions on Electron Devices, 2012, 59, 1928-1935.	3.3	56
49	Chemical and Mechanical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD Systems. Materials Research Society Symposia Proceedings, 2011, 68, .	0.1	2
50	Optical and Electrical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD systems. Materials Research Society Symposia Proceedings, 2011, 68, .	0.1	1
51	Ohmic and Quasi-Ohmic Contacts to Hydrogenated Amorphous Silicon Thin Films. Materials Research Society Symposia Proceedings, 2011, 70, .	0.1	2
52	Metal / Hydrogenated Amorphous Silicon Interfaces. Materials Research Society Symposia Proceedings, 2011, 95, .	0.1	2
53	Temperature Dependent Characteristics of Hydrogenated Amorphous Silicon thin film Transistors. Materials Research Society Symposia Proceedings, 2011, 118, .	0.1	6
54	Role of Hydrogen in Silicon Nitride Films Prepared by Various Deposition Techniques. Materials Research Society Symposia Proceedings, 2011, 118, .	0.1	5

#	ARTICLE	IF	CITATIONS
55	Properties of High Conductivity Phosphorous Doped Hydrogenated Microcrystalline Silicon and Application in Thin Film Transistor Technology. Materials Research Society Symposia Proceedings, 2011, 149, .	0.1	7
56	Properties and Application of Undoped Hydrogenated Microcrystalline Silicon Thin Films. Materials Research Society Symposia Proceedings, 2011, 149, .	0.1	1
57	Investigation of the Silicon Nitride on Hydrogenated Amorphous Silicon Interface. Materials Research Society Symposia Proceedings, 2011, 149, .	0.1	0
58	Correlations Between Optical, Electrical, and Structural Properties of In-Situ Phosphorus-Doped Hydrogenated Microcrystalline Silicon - Effects of Rapid Thermal Annealing on Material Properties. Materials Research Society Symposia Proceedings, 2011, 164, .	0.1	1
59	Paramagnetic Nitrogen Defects in Silicon Nitride. Materials Research Society Symposia Proceedings, 2011, 284, .	0.1	0
60	The Effect of UV Light on IR Absorption in Chemically Vapor Deposited a-SiNx:H Films. Materials Research Society Symposia Proceedings, 2011, 284, .	0.1	0
61	Performance of Polycrystalline Silicon Thin Film Transistors with Double Layer Gate Dielectric. Materials Research Society Symposia Proceedings, 2011, 284, .	0.1	0
62	Photobleaching of PL and Temperature Dependence of ESR in Nitrogen-Rich Amorphous Silicon Nitride Films. Materials Research Society Symposia Proceedings, 2011, 336, .	0.1	0
63	Low Temperature Deposition of Polycrystalline Silicon thin Films by Hot-Wire CVD. Materials Research Society Symposia Proceedings, 2011, 377, .	0.1	1
64	Atomic Hydrogen Effects on the Optical and Electrical Properties of Transparent Conducting Oxides For a-Si:H TFT-LCDs. Materials Research Society Symposia Proceedings, 2011, 424, .	0.1	2
65	High-Rate Deposited Amorphous Silicon Nitride for the Hydrogenated Amorphous Silicon Thin-Film Transistor Structures. Materials Research Society Symposia Proceedings, 2011, 424, .	0.1	0
66	Poly(bithiazole)s: A New Class of Conjugated Polymers for Polymer-Based Light-Emitting Diodes. Materials Research Society Symposia Proceedings, 2011, 424, .	0.1	1
67	Influence Of The Density of States and Series Resistance on the Field-Effect Activation Energy in a-Si:H TFT. Materials Research Society Symposia Proceedings, 2011, 424, .	0.1	3
68	Effects of Ultraviolet-Light on Polyimide Films for Liquid Crystal Alignment. Materials Research Society Symposia Proceedings, 2011, 508, .	0.1	0
69	A High-Voltage Hydrogenated Amorphous Silicon Thin-Film Transistor for Reflective Active-Matrix Cholesteric LCD. Materials Research Society Symposia Proceedings, 2011, 558, .	0.1	1
70	Electrical Properties and Stability of Dual-Gate Coplanar Homo Junction Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistor. Digest of Technical Papers SID International Symposium, 2011, 42, 1136-1139.	0.5	7
71	Electrical Instability of the a-Si:H TFTs Fabricated by Maskless Laser-Write Lithography on a Spherical Surface. IEEE Transactions on Electron Devices, 2011, 58, 160-164.	3.3	5
72	Electrical Properties and Stability of Dual-Gate Coplanar Homo Junction DC Sputtered Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors and Its Application to AM-OLEDs. IEEE Transactions on Electron Devices, 2011, 58, 4344-4353.	3.3	79

#	ARTICLE	IF	CITATIONS
73	Back channel etch chemistry of advanced a-Si:H TFTs. <i>Microelectronic Engineering</i> , 2011, 88, 207-212.	3.0	5
74	Analyte selective response in solution-deposited tetrabenzoporphyrin thin-film field-effect transistor sensors. <i>Sensors and Actuators B: Chemical</i> , 2011, 158, 333-339.	7.7	22
75	Electrical Stability of Power Efficient Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 120203.	2.0	1
76	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 091102.	2.0	17
77	Asymmetric Electrical Properties of Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistor and Its Applications to Flat Panel Displays. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 074203.	2.0	6
78	Asymmetric Electrical Properties of Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistor and Its Applications to Flat Panel Displays. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 074203.	2.0	7
79	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 091102.	2.0	25
80	Electrical Stability of Power Efficient Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 120203.	2.0	2
81	Hemispherical thin-film transistor passive pixel sensors. <i>Sensors and Actuators A: Physical</i> , 2010, 158, 280-283.	4.8	10
82	A maskless laser-write lithography processing of thin-film transistors on a hemispherical surface. <i>Microelectronic Engineering</i> , 2010, 87, 83-87.	3.0	21
83	Low frequency noise in long channel amorphous InGaZnO thin film transistors. <i>Journal of Applied Physics</i> , 2010, 108, .	2.3	75
84	Electrical Stability of Hexagonal a-Si:H TFTs. <i>IEEE Electron Device Letters</i> , 2010, 31, 53-55.	4.3	3
85	Two-dimensional numerical simulation of radio frequency sputter amorphous InGaZnO thin-film transistors. <i>Journal of Applied Physics</i> , 2009, 106, .	2.3	230
86	Asymmetric electrical properties of fork a-Si:H thin-film transistor and its application to flat panel displays. <i>Journal of Applied Physics</i> , 2009, 105, .	2.3	20
87	Amorphous InGaZnO Thin Film Transistor Current-Scaling Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 03B025.	2.0	27
88	Density of States of a-InGaZnO From Temperature-Dependent Field-Effect Studies. <i>IEEE Transactions on Electron Devices</i> , 2009, 56, 1177-1183.	3.3	158
89	Electrical Instability of RF Sputter Amorphous In-Ga-Zn-O Thin-Film Transistors. <i>Journal of Display Technology</i> , 2009, 5, 452-461.	1.6	103
90	P-11: DC/AC Electrical Instability of R.F. Sputter Amorphous In-Ga-Zn-O TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2009, 40, 1117.	0.5	16

#	ARTICLE	IF	CITATIONS
91	P14: AM-OLED Pixel Circuits Based on InGaZnO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2009, 40, 1128-1131.	0.5	18
92	Hexagonal a-Si:H TFTs: A New Advanced Technology for Flat-Panel Displays. IEEE Transactions on Electron Devices, 2008, 55, 329-336.	3.3	14
93	Advanced Amorphous Silicon Thin-Film Transistors for AM-OLEDs: Electrical Performance and Stability. IEEE Transactions on Electron Devices, 2008, 55, 1621-1629.	3.3	20
94	Dynamic Response of Normal and Corbino a-Si:H TFTs for AM-OLEDs. IEEE Transactions on Electron Devices, 2008, 55, 2338-2347.	3.3	15
95	Photofield-effect in amorphous InGaZnO (aIGZO) thin-film transistors. Journal of Information Display, 2008, 9, 21-29.	3.1	95
96	Advanced Multilayer Amorphous Silicon Thin-Film Transistor Structure: Film Thickness Effect on Its Electrical Performance and Contact Resistance. Japanese Journal of Applied Physics, 2008, 47, 3362-3367.	2.0	10
97	P13: Photosensitivity of Amorphous IGZO TFTs for Active-Matrix Flat-Panel Displays. Digest of Technical Papers SID International Symposium, 2008, 39, 1215-1218.	0.5	56
98	Novel Current-Scaling Current-Mirror Hydrogenated Amorphous Silicon Thin-Film Transistor Pixel Electrode Circuit with Cascade Capacitor for Active-Matrix Organic Light-Emitting Devices. Japanese Journal of Applied Physics, 2007, 46, 1343-1349.	2.0	12
99	Absolute photoluminescence quantum efficiency measurement of light-emitting thin films. Review of Scientific Instruments, 2007, 78, 096101.	1.6	37
100	Polycrystalline tetrabenzoporphyrin organic field-effect transistors with nanostructured channels. Applied Physics Letters, 2007, 90, 233107.	3.2	38
101	Solution-processed polycrystalline copper tetrabenzoporphyrin thin-film transistors. Synthetic Metals, 2007, 157, 190-197.	4.6	53
102	Asymmetric Electrical Properties of Corbino a-Si:H TFT and Concepts of Its Application to Flat Panel Displays. IEEE Transactions on Electron Devices, 2007, 54, 654-662.	3.3	29
103	Current-Scaling a-Si:H TFT Pixel-Electrode Circuit for AM-OLEDs: Electrical Properties and Stability. IEEE Transactions on Electron Devices, 2007, 54, 2403-2410.	3.3	21
104	70.3: Current-Scaling a-Si:H TFT Pixel Electrode Circuit for AM-OLEDs. Digest of Technical Papers SID International Symposium, 2006, 37, 1968.	0.5	0
105	Solution-processed nickel tetrabenzoporphyrin thin-film transistors. Journal of Applied Physics, 2006, 100, 034502.	2.3	60
106	P-143: A Novel Current-Scaling a-Si:H TFTs Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays. Digest of Technical Papers SID International Symposium, 2005, 36, 846.	0.5	3
107	Field-effect mobility of polycrystalline tetrabenzoporphyrin thin-film transistors. Journal of Applied Physics, 2005, 98, 014503.	2.3	86
108	Methanofullerene-coated tetrabenzoporphyrin organic field-effect transistors. Applied Physics Letters, 2005, 87, 173506.	3.2	14

#	ARTICLE	IF	CITATIONS
109	Poly(fluorene-oxadiazole) copolymer-based light-emitting devices on a plastic substrate. Synthetic Metals, 2005, 155, 1-10.	4.6	12
110	Transparent flexible plastic substrates for organic light-emitting devices. Journal of Electronic Materials, 2004, 33, 312-320.	2.4	36
111	Field-Effect Mobility of Organic Polymer Thin-Film Transistors. Chemistry of Materials, 2004, 16, 4699-4704.	6.9	47
112	Structural ordering and enhanced carrier mobility in organic polymer thin film transistors. Synthetic Metals, 2004, 146, 181-185.	4.6	104
113	Electrical Behavior of Organic Transistors and Circuits. , 2004, , 347-524.		4
114	Angular dependence of the luminance and contrast in medical monochrome liquid crystal displays. Medical Physics, 2003, 30, 2602-2613.	3.4	34
115	Integrating sphere charge coupled device-based measurement method for organic light-emitting devices. Review of Scientific Instruments, 2003, 74, 3572-3575.	1.6	12
116	Optoelectrical properties of four amorphous silicon thin-film transistors 200 dpi active-matrix organic polymer light-emitting display. Applied Physics Letters, 2003, 83, 3233-3235.	3.2	12
117	An integrating sphere CCD-based measurement method of the OP-LED opto-electronic characteristics. , 2003, , .		0
118	Contact Resistance in Schottky Contact Gated-Four-Probe a-Si Thin-Film Transistor. Japanese Journal of Applied Physics, 2003, 42, L907-L909.	2.0	8
119	Efficient and saturated blue organic polymer light emitting devices with an oxadiazole containing poly(fluorene) polymer emissive layer. , 2003, , .		1
120	Monte Carlo modeling of organic polymer light-emitting devices on flexible plastic substrates. , 2003, , .		5
121	Structural ordering in F8T2 polyfluorene thin film transistors. , 2003, , .		11
122	Influence of gate dielectrics on electrical properties of F8T2 polyfluorene thin film transistors. , 2003, , .		12
123	25.1: Luminance Probes for Contrast Measurements in Medical Displays. Digest of Technical Papers SID International Symposium, 2003, 34, 928.	0.5	3
124	4.5: 200 dpi 4-a-Si:H TFTs Current-Driven AM-PLEDs. Digest of Technical Papers SID International Symposium, 2003, 34, 22.	0.5	0
125	Organic polymer thin film phototransistors. , 2003, , .		2
126	Time dependence of organic polymer thin film transistor current. , 2003, , .		1

#	ARTICLE	IF	CITATIONS
127	4.4: 200 dpi 3-a-Si:H TFTs Voltage-Driven AM-PLEDs. Digest of Technical Papers SID International Symposium, 2003, 34, 18.	0.5	4
128	Source / drain contacts in organic polymer thin film transistors. Materials Research Society Symposia Proceedings, 2003, 771, .	0.1	1
129	Effect of Illumination on Organic Polymer Thin-Film Transistors. Materials Research Society Symposia Proceedings, 2003, 771, .	0.1	4
130	Air-stable organic polymer red light-emitting devices on flexible plastic substrates. , 2002, , .		4
131	High-resolution organic polymer light-emitting pixels fabricated by imprinting technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 2877.	1.7	49
132	<title>Characterization of a high-quality monochrome AM-LCD monitor for digital radiology</title>. , 2002, , .		7
133	P-102: Amorphous Silicon Thin-Film Transistors-based Active-Matrix Organic Light-Emitting Displays. Digest of Technical Papers SID International Symposium, 2002, 33, 614.	0.5	2
134	P-103: Novel Poly-Si TFT Pixel Electrode Circuits and Current Programmed Active-Matrix Driving Methods for AM-OLEDs. Digest of Technical Papers SID International Symposium, 2002, 33, 618.	0.5	12
135	<title>Amorphous silicon thin-film transistor-based active-matrix organic light-emitting displays for medical imaging</title>. , 2002, , .		4
136	Gate-planarized organic polymer thin film transistors. Journal of Electronic Materials, 2002, 31, 512-519.	2.4	11
137	Accurate small-spot luminance measurements. Displays, 2002, 23, 177-182.	3.7	10
138	Influence of the Amorphous Silicon Thickness on Top Gate Thin-Film Transistor Electrical Performances. Japanese Journal of Applied Physics, 2001, 40, 530-537.	2.0	69
139	Materials and device structures for high-performance poly OLEDs on flexible plastic substrates. , 2001, , .		3
140	<title>Characterization of crosstalk in high-resolution active matrix liquid crystal displays for medical imaging</title>. , 2001, , .		2
141	<title>Color and contrast perception in monochrome medical imaging flat-panel displays</title>. , 2001, , .		0
142	Polyfluorene light-emitting devices on flexible plastic substrates. , 2001, , .		1
143	<title>a-Si:H pixel electrode circuits for AM-OLEDs</title>. , 2001, , .		0
144	Four-Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays. Japanese Journal of Applied Physics, 2001, 40, 1199-1208.	2.0	56

#	ARTICLE	IF	CITATIONS
145	Monte Carlo analysis of the spectral photon emission and extraction efficiency of organic light-emitting devices. <i>Journal of Applied Physics</i> , 2001, 90, 1827-1830.	2.3	34
146	<title>Advanced amorphous silicon thin film transistor active-matrix organic light-emitting displays design for medical imaging</title>. , 2001, , .		2
147	Interference fringe-free transmission spectroscopy of amorphous thin films. <i>Journal of Applied Physics</i> , 2000, 88, 5764-5771.	2.3	15
148	High-efficiency organic polymer light-emitting heterostructure devices on flexible plastic substrates. <i>Applied Physics Letters</i> , 2000, 76, 661-663.	3.2	100
149	Light output measurements of the organic light-emitting devices. <i>Review of Scientific Instruments</i> , 2000, 71, 2104-2107.	1.6	18
150	Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon Thin-Film Transistor Characteristics. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2251-2255.	2.0	42
151	Ultraviolet-light Induced Liquid-Crystal Alignment on Polyimide Films. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 5996-6004.	2.0	22
152	A Novel Structure to Improve the Viewing Angle Characteristics of Twisted-Nematic Liquid Crystal Displays. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 4110-4116.	2.0	2
153	Microstructure characterization of amorphous thin solid films in a fringe-free environment. <i>Journal of Applied Physics</i> , 1999, 85, 388-396.	2.3	5
154	Method of collecting pure vibrational absorption spectra of amorphous thin films. <i>Thin Solid Films</i> , 1999, 349, 283-288.	1.9	2
155	Thin film transistors in low temperature as-deposited and reduced-crystallization-time polysilicon on 665Å°C strain point glass substrates. <i>Thin Solid Films</i> , 1999, 338, 281-285.	1.9	10
156	Tuning Optical and Electronic Properties of Bithiazole Containing Polymers by N-Methylation. <i>Macromolecules</i> , 1999, 32, 2484-2489.	5.2	24
157	Small Spot Contrast Measurements in High Performance Displays. <i>Digest of Technical Papers SID International Symposium</i> , 1999, 30, 516.	0.5	1
158	<title>Organic polymer light-emitting devices on plastic substrates</title>. , 1999, , .		0
159	Monte carlo modeling method for light transport in organic thin film light-emitting devices. , 1999, , SuD2.		1
160	Synthesis and Characterization of Conjugated, n-Dopable, Bithiazole-Containing Polymers. <i>Chemistry of Materials</i> , 1998, 10, 1713-1719.	6.9	50
161	Observation of incident angle dependent phonon absorption in hydrogenated amorphous silicon nitride thin films. <i>Applied Physics Letters</i> , 1998, 73, 3866-3868.	3.2	16
162	Investigation of intrinsic channel characteristics of hydrogenated amorphous silicon thin-film transistors by gated-four-probe structure. <i>Applied Physics Letters</i> , 1998, 72, 2874-2876.	3.2	24

#	ARTICLE	IF	CITATIONS
163	Electrical Instability of Hydrogenated Amorphous Silicon Thin-Film Transistors for Active-Matrix Liquid-Crystal Displays. Japanese Journal of Applied Physics, 1998, 37, 4704-4710.	2.0	99
164	Top-Gate Staggered Amorphous Silicon Thin-Film Transistors: Series Resistance and Nitride Thickness Effects. Japanese Journal of Applied Physics, 1998, 37, 5914-5920.	2.0	82
165	Effect of secondary radiations on the performance of digital radiographic detectors. , 1998, , .		9
166	<title>Viewing-angle improvement with compensation films for LCDs</title>. , 1998, , .		1
167	High-performance top-gate a-Si:H TFTs for AMLCDs. Digest of Technical Papers SID International Symposium, 1998, 29, 383.	0.5	2
168	<title>Planarization technology of a-Si:H TFTs for AM LCDs</title>. , 1998, , .		7
169	Full-Color Light-Emitting Devices Based on ĩ€- and ĩƒ-Conjugated Polymer Materials. Digest of Technical Papers SID International Symposium, 1998, 29, 663.	0.5	2
170	Longitudinal Vibrational Absorption Modes of Hydrogenated Amorphous Silicon Nitride Thin Films. Materials Research Society Symposia Proceedings, 1998, 507, .	0.1	0
171	<title>Gated four-probe TFT structure: a new technique to measure the intrinsic performance of a-Si:H TFT</title>. , 1997, , .		1
172	Aluminum Gate Metallization for AMLCDs. Materials Research Society Symposia Proceedings, 1997, 471, .	0.1	3
173	Electrical Characteristics of New LDD Poly-Si TFT with MIS-Alignment Tolerant Structure for AMLCDs. Materials Research Society Symposia Proceedings, 1997, 471, .	0.1	0
174	Electrical and Optical Properties of Low Dielectric Constant Planarization Polymer for High-Aperture-Ratio a-Si:H TFT-LCDs. Materials Research Society Symposia Proceedings, 1997, 471, .	0.1	8
175	ITO surface ball formation induced by atomic hydrogen in PECVD and HW-CVD tools. Thin Solid Films, 1997, 304, 123-129.	1.9	37
176	Direct determination of the quadratic electro-optic coefficient in an a-Si:H based waveguide. Journal of Non-Crystalline Solids, 1996, 198-200, 107-110.	3.3	12
177	Study of sub-bandgap photo-induced absorption in a-Si:H using excitation spectroscopy in a waveguide configuration. Journal of Non-Crystalline Solids, 1996, 198-200, 259-262.	3.3	4
178	Patterning of transparent conducting oxide thin films by wet etching for a-Si:H TFT-LCDs. Journal of Electronic Materials, 1996, 25, 1806-1817.	2.4	43
179	Paramagnetic point defects in silicon nitride and silicon oxynitride thin films on silicon. Colloids and Surfaces A: Physicochemical and Engineering Aspects, 1996, 115, 311-317.	5.2	20
180	Creation and Properties of Nitrogen Dangling Bond Defects in Silicon Nitride Thin Films. Journal of the Electrochemical Society, 1996, 143, 3685-3691.	3.1	28

#	ARTICLE	IF	CITATIONS
181	Selective Deposition of Polycrystalline Silicon Thin Films by Hot-Wire CVD. Materials Research Society Symposia Proceedings, 1995, 403, .	0.1	0
182	Photoluminescence and electron spin resonance in nitrogen-rich amorphous silicon nitride. Journal of Non-Crystalline Solids, 1995, 182, 103-108.	3.3	10
183	Nature of the Si and N dangling bonds in silicon nitride. Journal of Non-Crystalline Solids, 1995, 187, 297-300.	3.3	44
184	Preface. Journal of Non-Crystalline Solids, 1995, 187, vii.	3.3	0
185	Temperature dependence of the electron-spin resonance in nitrogen-rich amorphous silicon nitride. Physical Review B, 1994, 49, 13420-13422.	3.2	9
186	Photocreation and photobleaching of a-Si N1.6:H/c-Si interface states studied by photocapacitance transient spectroscopy. Physica B: Condensed Matter, 1993, 185, 542-545.	2.8	0
187	Defects in amorphous hydrogenated silicon nitride films. Journal of Non-Crystalline Solids, 1993, 164-166, 1055-1060.	3.3	20
188	Optically Induced Nitrogen Dangling Bonds in Amorphous Hydrogenated Silicon Nitride Thin Films. , 1993, , 421-426.		0
189	Photocreation and photobleaching of a-Si N1.6:H/c-Si interface states studied by photocapacitance transient spectroscopy. , 1993, , 542-545.		0
190	Near-ir absorption in chemically vapor deposited a-SiNx:H films. Physical Review B, 1992, 46, 15163-15168.	3.2	8
191	Photoluminescence in Nitrogen-Rich a-SiN <sub>x</sub> :H. Materials Research Society Symposia Proceedings, 1992, 258, .	0.1	9
192	Paramagnetic Point Defects in Amorphous Silicon Dioxide and Amorphous Silicon Nitride Thin Films: II .. Journal of the Electrochemical Society, 1992, 139, 880-889.	3.1	103
193	Investigations on the quality of polysilicon film-gate dielectric interface in polysilicon thin film transistors. Thin Solid Films, 1992, 216, 137-141.	1.9	13
194	Microscopic origin of the light-induced defects in hydrogenated nitrogen-rich amorphous silicon nitride films. Journal of Non-Crystalline Solids, 1991, 137-138, 291-294.	3.3	55
195	Determination of electron and hole mobilities in an a-Si:H from photo-electric effects in a waveguide structure. Journal of Non-Crystalline Solids, 1991, 137-138, 455-458.	3.3	2
196	Transient photocapacitance and capacitance studies of interface and bulk states in metal / a-SiN1.6:H / a-Si:H / c-Si devices. Journal of Non-Crystalline Solids, 1991, 137-138, 1051-1054.	3.3	4
197	Thermal Annealing of Light-Induced K Centers in Hydrogenated Amorphous Silicon Nitride. Materials Research Society Symposia Proceedings, 1991, 219, .	0.1	2
198	Influence of the Gate Bias and Temperature on Positive Charge Generation in TFT Gate-Quality Amorphous Silicon Nitride Films. Materials Research Society Symposia Proceedings, 1991, 219, .	0.1	3

#	ARTICLE	IF	CITATIONS
199	Bias Stress Induced Instabilities in Amorphous Silicon Nitride / Crystalline Silicon and Amorphous Silicon Nitride / Amorphous Silicon Structures. Materials Research Society Symposia Proceedings, 1991, 219, .	0.1	5
200	Structural identification of the silicon and nitrogen dangling bond centers in amorphous silicon nitride. Journal of Applied Physics, 1991, 70, 346-354.	2.3	76
201	Optically Induced Paramagnetism in Amorphous Hydrogenated Silicon Nitride Thin Films. Materials Research Society Symposia Proceedings, 1991, 242, .	0.1	7
202	Structure, Characteristics, and the Application of Phosphorus Doped Hydrogenated Microcrystalline Silicon. Materials Research Society Symposia Proceedings, 1991, 242, .	0.1	0
203	Effect of Gate Dielectric on Performance of Polysilicon thin Film Transistors. Materials Research Society Symposia Proceedings, 1990, 182, .	0.1	10
204	The Generation and Bleaching of Positive Charge in Gate-Quality Nitrogen-Rich Amorphous Silicon Nitride By Sub-Bandgap Illumination. Materials Research Society Symposia Proceedings, 1990, 192, .	0.1	3
205	The nature of the dominant deep trap in amorphous silicon nitride films: Evidence for a negative correlation energy. Applied Surface Science, 1989, 39, 392-405.	6.6	66
206	Electron spin resonance study of metal-nitride-silicon structures: Observation of Si dangling bonds with different configurations and trapping properties in silicon nitride. Applied Surface Science, 1989, 39, 412-419.	6.6	7
207	Gate dielectric and contact effects in hydrogenated amorphous silicon-silicon nitride thin film transistors. Journal of Applied Physics, 1989, 65, 3951-3957.	2.3	118
208	Light-induced effects in hydrogenated amorphous nitrogen-rich silicon nitride films. Journal of Non-Crystalline Solids, 1989, 114, 612-614.	3.3	12
209	Nature of the dominant deep trap in amorphous silicon nitride. Physical Review B, 1988, 38, 8226-8229.	3.2	93
210	Contact resistance to undoped and phosphorus-doped hydrogenated amorphous silicon films. Applied Physics Letters, 1988, 53, 1943-1945.	3.2	45
211	Electron Spin Resonance Spectroscopy Of Defects In Low Temperature Dielectric Films. Proceedings of SPIE, 1988, , .	0.0	2
212	Minority Carrier Injection and Series Resistance Effects in Hydrogenated Amorphous Silicon Schottky Barrier Diodes. Materials Research Society Symposia Proceedings, 1985, 49, .	0.1	3
213	Far UV pulsed laser melting of silicon. Applied Physics Letters, 1985, 46, 547-549.	3.2	56
214	Optical, electrical and contact properties of homoCVD a-Si:H films. Journal of Non-Crystalline Solids, 1985, 77-78, 789-792.	3.3	6
215	Schottky Barrier Formation at Metal-Hydrogenated Amorphous Silicon Interfaces. , 1985, , 183-187.		0
216	Electrical and photovoltaic properties of trans-polyacetylene. Journal Physics D: Applied Physics, 1984, 17, 805-817.	3.1	8

#	ARTICLE	IF	CITATIONS
217	Electrical and photovoltaic properties of metal contacts to trans-polyacetylene. Thin Solid Films, 1984, 113, 1-14.	1.9	8
218	Transport properties and defect states of a-Si:H grown by HOMOCVD. Journal of Non-Crystalline Solids, 1984, 66, 51-58.	3.3	6
219	Metal - Polyacetylene Schottky Barrier Diodes. Molecular Crystals and Liquid Crystals, 1984, 105, 203-217.	1.2	46
220	Photovoltaic properties of In/trans-polyacetylene/Electrodag+502 Schottky barrier cells. Solar Cells, 1983, 9, 281-288.	0.8	4
221	REVIEW OF CONDUCTOR-POLYMERIC SEMICONDUCTOR SOLAR CELLS. Journal De Physique Colloque, 1983, 44, C3-529-C3-535.	0.0	0
222	Photovoltaic and rectification properties of In/trans-(CH) <sub>x</sub> /electrodag +502 schottky-barrier cells. Molecular Crystals and Liquid Crystals, 1982, 83, 319-327.	1.1	9
223	Novel approach to the study of electrical conduction in bromine-doped polyacetylene. Thin Solid Films, 1982, 92, 243-251.	1.9	5
224	Organic Photovoltaic Materials: Polyacetylene. , 1982, , 562-567.		0
225	Electrical conductivity and infrared absorption of trans- polyacetylene in the presence of iodine. Journal of the Chemical Society, Faraday Transactions 2, 1981, 77, 2157-2168.	1.1	13
226	Junction formation between undoped polyacetylene and metals. European Polymer Journal, 1980, 16, 677-678.	6.0	8
227	Hydrogenated amorphous-silicon thin-film transistor structure with buried field plate. , 0, , .		2